



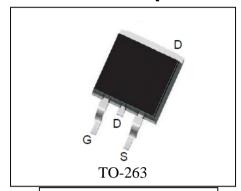
Features

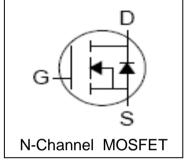
- 68V/88A, RDS (ON) = $6m\Omega$ (Typ.) @ VGS=10V
- Ultra Low On-Resistance
- Exceptional dv/dt capability
- Fast Switching and Fully Avalanche Rated
- 100% avalanche tested
- 175°C Operating Temperature
- Lead Free and Green Available

Applications

- Switching Application Systems
- Inverter Systems

Pin Description





Absolute Maximum Ratings

Symbol	Parameter	Rating	Unit			
Common Ratin	gs (T _A =25°C Unless Otherwise Noted)					
V_{DSS}	Drain-Source Voltage	68	V			
V_{GSS}	Gate-Source Voltage		±25	v		
TJ	Maximum Junction Temperature		175	°C		
T_{STG}	Storage Temperature Range		-55 to 175	°C		
I _S	Diode Continuous Forward Current	T _C =25°C	88	Α		
ounted on La	rge Heat Sink		<u> </u>			
I _{DP}	300µs Pulse Drain Current Tested	T _C =25°C	320	А		
1.	Continuous Proin Current()/ 10)()	T _C =25°C	88	А		
I _D	Continuous Drain Current(V _{GS} =10V)	T _C =100°C	65	А		
P_D	Maniero Barres Bianieria	T _C =25°C	120	10/		
	Maximum Power Dissipation	T _C =100°C	60	W		
$R_{ heta JC}$	Thermal Resistance-Junction to Case	1.25	°C/W			
rain-Source A	valanche Ratings					
E _{AS}	Avalanche Energy, Single Pulsed		225	mJ		



Electrical Characteristics (T_A=25°C Unless Otherwise Noted)

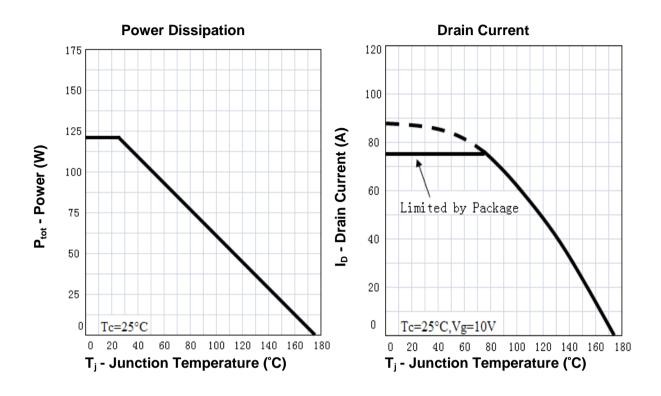
0	Donomoton	Toot Condition	ı	1111		
Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Unit
Static Cha	aracteristics					
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =250μA	68			V
	Zoro Coto Voltago Drain Current	V_{DS} = 68V, V_{GS} =0V			1	
I _{DSS}	Zero Gate Voltage Drain Current	T _J =85°C			30	μΑ
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$, $I_{DS}=250\mu A$	2	3	4	V
I _{GSS}	Gate Leakage Current	V_{GS} =±25V, V_{DS} =0V			±100	nA
R _{DS(ON)}	Drain-Source On-state Resistance	V _{GS} = 10V, I _{DS} =40A		6	8	mΩ
Diode Cha	aracteristics					
V _{SD}	Diode Forward Voltage	I _{SD} =40A, V _{GS} =0V			1.2	V
trr	Reverse Recovery Time	Isb=40A, dlsb/dt=100A/μs		49		ns
Qrr	Reverse Recovery Charge	-15D=40A, αιδυ/αι=100A/μ5		93		nC
Dvnamic	⑤ Characteristics					
R _G	Gate Resistance	V _{GS} =0V,V _{DS} =0V,F=1MHz		1.4		Ω
C _{iss}	Input Capacitance	Vgs=0V,		2900		
C _{oss}	Output Capacitance	V _{DS} =30V,		340		pF
C _{rss}	Reverse Transfer Capacitance	Frequency=1.0MHz		200		
t _{d(ON)}	Turn-on Delay Time			13		
t _r	Turn-on Rise Time	Vdd=30V, Rl=0.8Ω, Ids=40A, Vgen= 10V,		15		ns
$t_{d(OFF)}$	Turn-off Delay Time	$R_{G}=8\Omega$		29		
t _f	Turn-off Fall Time			55		
Gate Chai	rge Characteristics 5					
Qg	Total Gate Charge			65		
Q_{gs}	Gate-Source Charge	Vps=54V, Vgs= 10V, lps=40A		12		nC
Q_{gd}	Gate-Drain Charge	1071		21		

- Notes: ①Calculated continuous current based on maximum allowable junction temperature. The package limitation current is 75A.
 - 2) Pulse width limited by safe operating area.

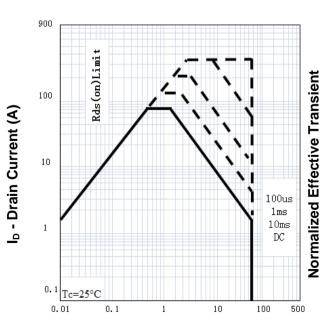
 - (4) Pulse test; Pulse width≤300µs, duty cycle≤2%.
 - ⑤Guaranteed by design, not subject to production testing.



Typical Characteristics

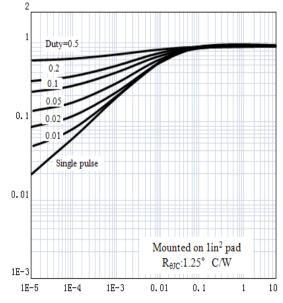


Safe Operation Area



V_{DS} - Drain-Source Voltage (V)

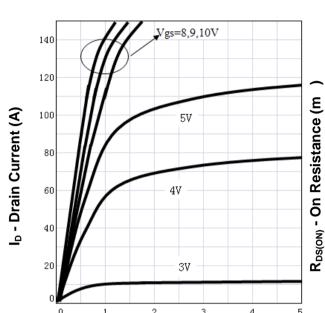
Thermal Transient Impedance



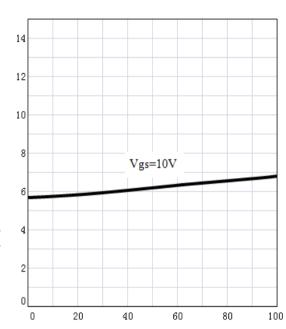
Square Wave Pulse Duration (sec)



Typical Characteristics



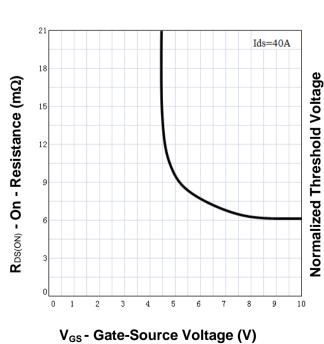
Output Characteristics Drain-Source On Resistance



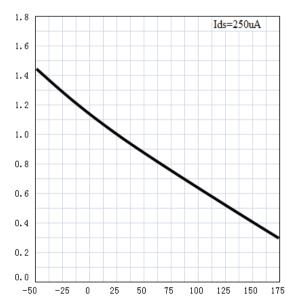
V_{DS} - Drain-Source Voltage (V)

I_D - Drain Current (A)

Drain-Source On Resistance



Gate Threshold Voltage

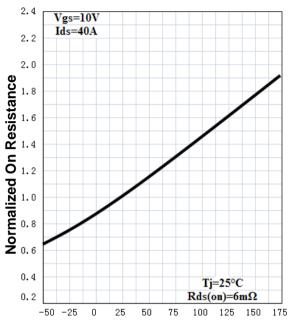


T_j - Junction Temperature (°C)



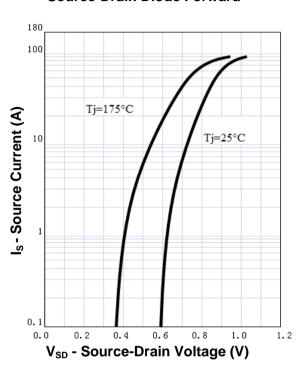
Typical Characteristics

Drain-Source On Resistance

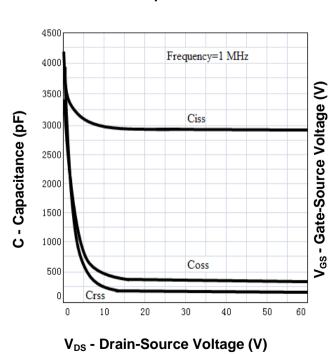


T_i - Junction Temperature (°C)

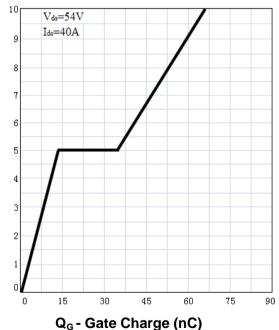
Source-Drain Diode Forward



Capacitance

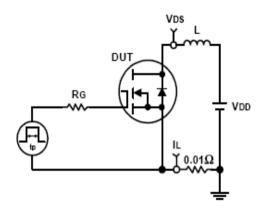


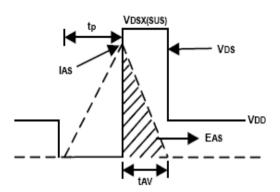
Gate Charge



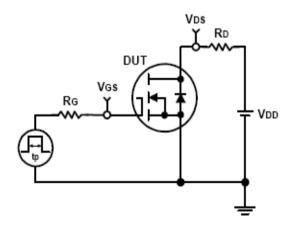


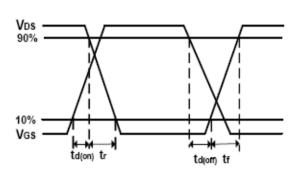
Avalanche Test Circuit and Waveforms





Switching Time Test Circuit and Waveforms







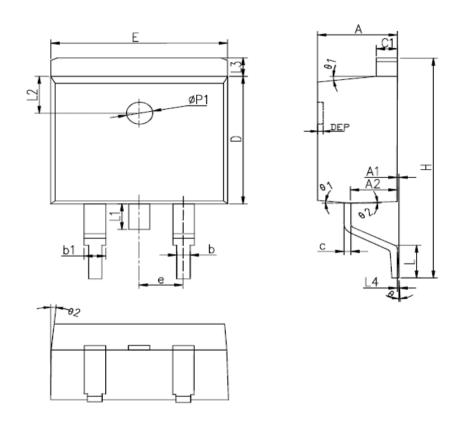
Ordering and Marking Information

Device	Marking	Package	Packaging	ckaging Quantity Reel Size		Tape width	
RU6888S	RU6888S	TO-263	Tube	50	-	-	
RU6888S-R	RU6888S	TO-263	Tape&Reel	800	13"	24mm	



Package Information

TO-263-2L



gyn (Dol	MM		INCH			MM		INCH					
SYMBOL	MIN	NOM	MAX	MIN	NOM	MAX	SYMBOL	MIN	NOM	MAX	MIN	NOM	MAX
A	4.40	4.57	4.70	0.173	0.180	0.185	L	2.00	2.30	2.60	0.079	0.090	0.102
A1	0	0.10	0.25	0	0.004	0.010	L3	1.17	1.27	1.40	0.046	0.050	0.055
A2	2.59	2.69	2.79	0.102	0.106	0.110	L1	-	-	1.70	-	-	0.067
b	0.77	-	0.90	0.030	-	0.035	L4	0.25BSC			0.01BSC		
b1	1.23	-	1.36	0.048	-	0.052	L2	2.50REF.		0.098REF.			
с	0.34	-	0.47	0.013	-	0.019	θ	0°	-	8°	0°	-	8°
C1	1.22	-	1.32	0.048	-	0.052	θ 1	5°	7°	9°	5°	7°	9°
D	8.60	8.70	8.80	0.338	0.343	0.346	θ 2	1°	3°	5°	1°	3°	5°
Е	10.00	10.16	10.26	0.394	0.4	0.404	DEP	0.05	0.10	0.20	0.002	0.004	0.008
e		2.54BSC		0.1BSC		Øp1	1.40	1.50	1.60	0.055	0.059	0.063	
Н	14.70	15.10	15.50	0.579	0.594	0.610							

ALL DIMENSIONS REFER TO JEDEC STANDARD DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS



Customer Service

Worldwide Sales and Service:

Sales@ruichips.com

Technical Support:

Technical@ruichips.com

Investor Relations Contacts:

Investor@ruichips.com

Marcom Contact:

Marcom@ruichips.com

Editorial Contact:

Editorial@ruichips.com

HR Contact:

HR@ruichips.com

Legal Contact:

Legal@ruichips.com

Shen Zhen RUICHIPS Semiconductor CO., LTD

Room 501, the 5floor An Tong Industrial Building, NO.207 Mei Hua Road Fu Tian Area Shen Zhen City, CHINA

TEL: (86-755) 8311-5334 **FAX:** (86-755) 8311-4278 **E-mail:** Sales-SZ@ruichips.com